



DCR390J85

Phase Control Thyristor

Replaces DS5833-3 DS5833-4 June 2014 (LN31648)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR390J85* DCR390J80 DCR390J70	8500 8000 7000	$\begin{split} T_{vj} &= \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ I_{DRM} &= I_{RRM} = 100\text{mA}, \\ V_{DRM}, V_{RRM} t_p &= 10\text{ms}, \\ V_{DSM} \& V_{RSM} &= \\ V_{DRM} \& V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available. *8200V @ -40° C, 8500V @ 0° C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR390J85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	8500V
$I_{T(AV)}$	387A
I _{TSM}	5250A
dV/dt*	1500V/µs
dl/dt	200A/us

* Higher dV/dt selections available

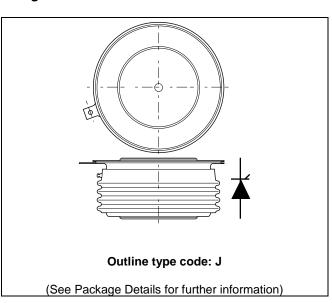


Fig. 1 Package outline

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CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Sid	de Cooled			
I _{T(AV)}	Mean on-state current	Half wave resistive load	387	А
I _{T(RMS)}	RMS value	-	608	А
Ι _Τ	Continuous (direct) on-state current	-	583	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	5.25	kA
l ² t	I ² t for fusing	$V_R = 0$	0.138	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.0379	°C/W
		Single side cooled	Anode DC	-	0.0745	°C/W
			Cathode DC	-	0.0797	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 11.5kN	Double side	-	0.0072	°C/W
		(with mounting compound)	Single side	-	.0144	°C/W
T_{vj}	Virtual junction temperature	Blocking V _{DRM} / _{VRRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
F _m	Clamping force			10	13	kN

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DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditio	Test Conditions		Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	100	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)}	Repetitive 50Hz	-	100	A/µs
		Gate source 30V, 10Ω ,	Non-repetitive	-	200	A/µs
		$t_r < 0.5 \mu s, T_j = 125^{\circ}C$				
$V_{T(TO)}$	Threshold voltage – Low level	50A to 400A at T _{case} = 125°C	;	-	1.162	V
	Threshold voltage – High level	400A to 1600A at T _{case} = 125	5°C	-	1.3063	٧
r _T	On-state slope resistance – Low level	50A to 400A at T _{case} = 125°C		-	3.153	mΩ
	On-state slope resistance – High level	400A to 1600A at T _{case} = 125°C		-	2.763	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10Ω		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 125$ °C, $V_R = 100$ V, $dI/dt = 5$ A/ μ s,		-	1200	μs
		dV _{DR} /dt = 20V/μs linear				
Qs	Stored charge	$I_T = 500A$, $T_j = 125$ °C, $dI/dt = 5A/\mu s$,		2000	3000	μC
IL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
I _H	Holding current	$T_j = 25^{\circ}\text{C}, R_{G-K} = \infty, I_{TM} = 50^{\circ}$	0A, I _T = 5A	-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25$ °C	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25$ °C	350	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	15	mA

CURVES

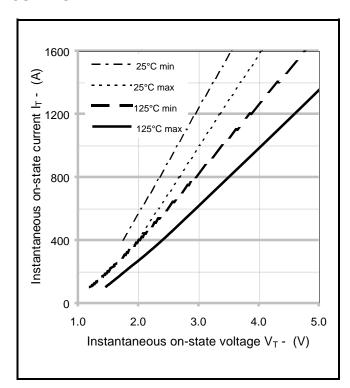


Fig.2 Maximum & minimum on-state characteristics

these values are valid for $T_j = 125$ °C for $I_T 50$ A to 1600A

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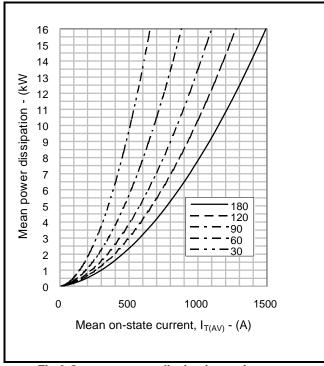


Fig.3 On-state power dissipation - sine wave

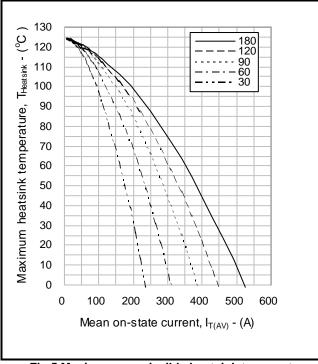
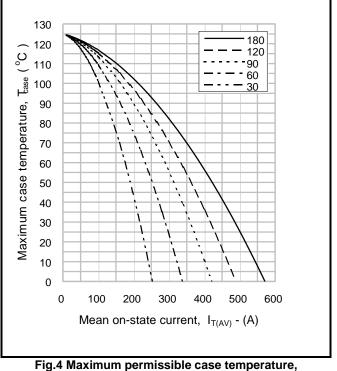


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave



double side cooled – sine wave

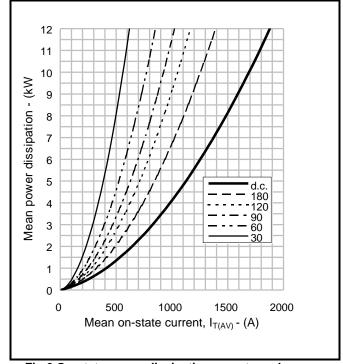


Fig.6 On-state power dissipation - rectangular wave

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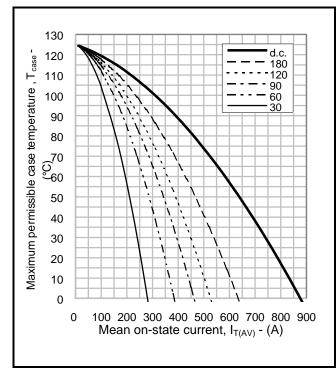


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

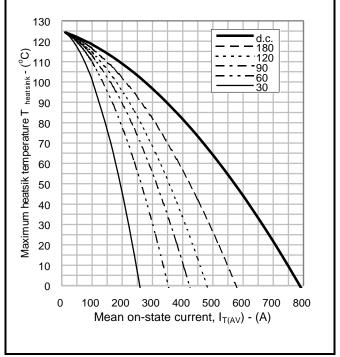
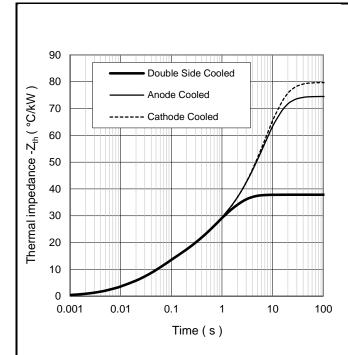


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave



		1	2	3	4
Double side cooled	R _i (°C/kW)	2.4256	9.3503	10.6963	15.3758
	T _i (s)	0.0087759	0.053099	0.4497246	1.395
Anode side cooled	R _i (°C/kW)	2.8091	9.5576	11.3564	50.6136
	T _i (s)	0.0097443	0.0591913	0.4759179	6.5548
Cathode side cooled	R _i (°C/kW)	2.9507	9.4031	11.0771	56.0405
	T _i (s)	0.0100391	0.0606056	0.4732916	7.228

 $Z_{th} = \sum [R_i x (1-exp. (t/t_i))]$ [1]

 $\Delta R_{th(j-c)}$ Conduction

Tables show the increments of thermal resistance $R_{\text{th(j-c)}}$ when the device operates at conduction angles other than d.c.

Double side cooling				
	$\Delta Z_{th}(z)$			
θ°	sine.	rect.		
180	4.43	3.01		
120	5.13	4.30		
90	5.89	5.03		
60	6.58	5.81		
30	7.12	6.67		
15	7 36	7 13		

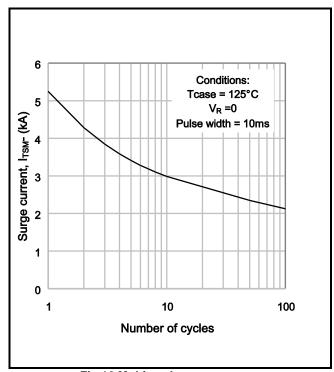
Anode Side Cooling			
	$\Delta Z_{th}(z)$		
θ°	sine.	rect.	
180	4.39	2.99	
120	5.07	4.26	
90	5.81	4.97	
60	6.48	5.74	
30	7.00	6.57	
15	7.24	7.01	

Cathode Sided Cooling			
	ΔZ_{th} (z)		
θ°	sine.	rect.	
180	4.37	2.98	
120	5.05	4.25	
90	5.79	4.96	
60	6.45	5.72	
30	6.97	6.54	
4.5	7 00	0.00	

Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)

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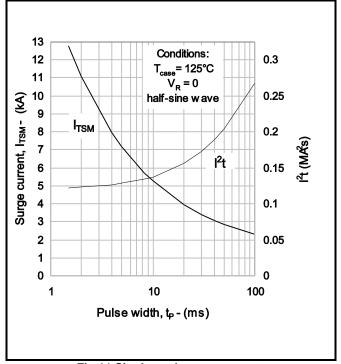


Fig.11 Single-cycle surge current

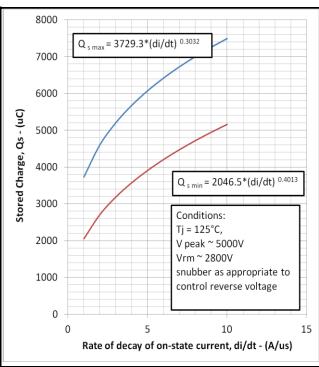


Fig.12 Stored charge

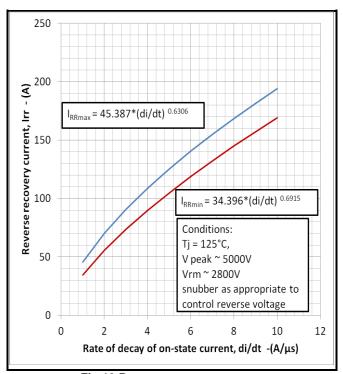


Fig.13 Reverse recovery current

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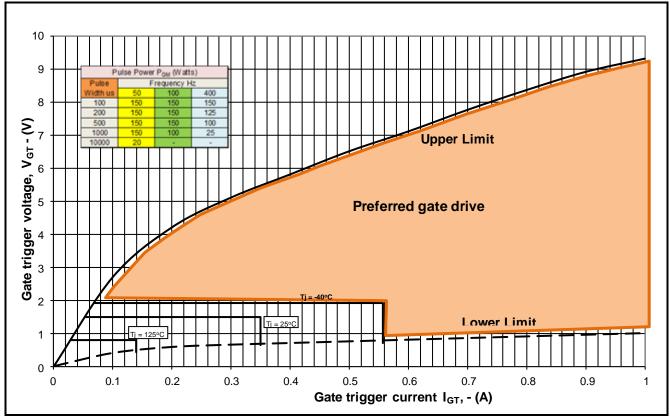


Fig14 Gate Characteristics

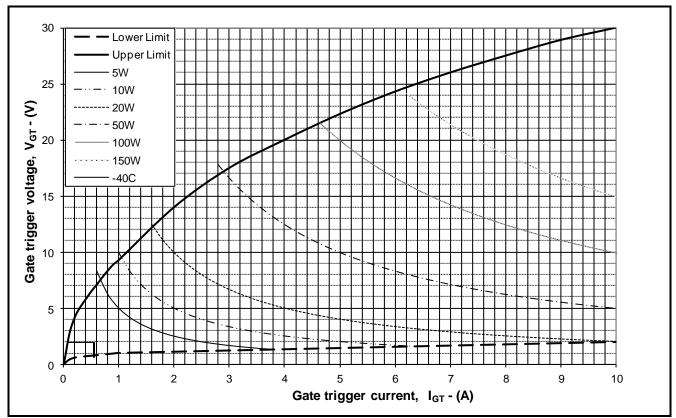


Fig. 15 Gate characteristics

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PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

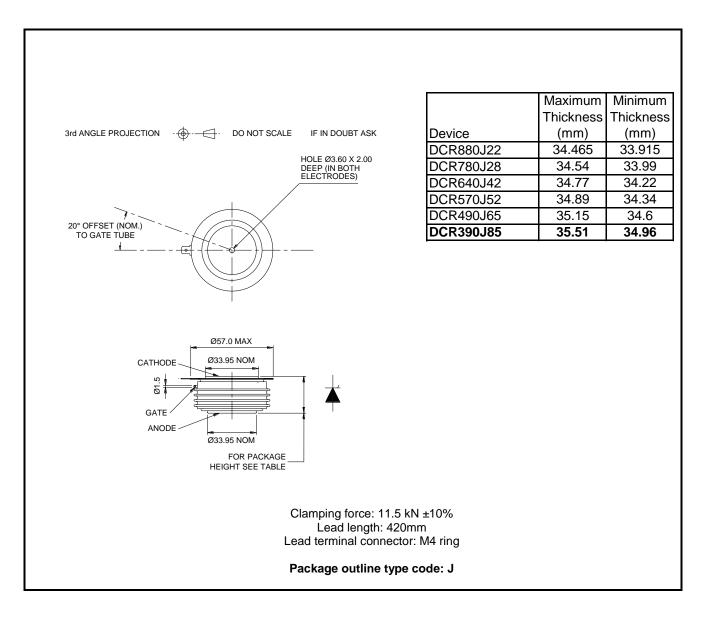


Fig.16 Package outline

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HEADQUARTERS OPERATIONS

DYNEX SEMICONDUCTOR LIMITED
Doddington Road, Lincoln, Lincolnshire, LN6 3LF
United Kingdom.
Phone: +44 (0) 1522 500500

Phone: +44 (0) 1522 500500 Web: http://www.dynexsemi.com

CUSTOMER SERVICE

Phone: +44 (0) 1522 502753 / 502901 e-mail: powersolutions@dynexsemi.com

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